

# C. U. SHAH UNIVERSITY

## Winter Examination-2022

**Subject Name : Advances in Solid State Electronic Devices**

**Subject Code : 5SC04ASS1**

**Branch: M.Sc. (Physics)**

**Semester: 4**

**Date: 19/09/2022**

**Time: 02:30 To 05:30**

**Marks: 70**

**Instructions:**

- (1) Use of Programmable calculator and any other electronic instrument is prohibited.
  - (2) Instructions written on main answer book are strictly to be obeyed.
  - (3) Draw neat diagrams and figures (if necessary) at right places.
  - (4) Assume suitable data if needed.
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### SECTION – I

- |                |   |                 |
|----------------|---|-----------------|
| <b>Q-1</b>     | <b>Attempt the Following questions</b>  | <b>(07)</b>     |
|                | <b>a.</b> List the demands for Bipolar devices.   | <b>01</b>       |
|                | <b>b.</b> What problems are observed in Bipolar devices?  | <b>01</b>       |
|                | <b>c.</b> What is the full form of HBTs?  | <b>01</b>       |
|                | <b>d.</b> What is the solution for the Bipolar devices?   | <b>01</b>       |
|                | <b>e.</b> Band gap of polysilicon is?   | <b>01</b>       |
|                | <b>f.</b> Define JFET.  | <b>01</b>       |
|                | <b>g.</b> List the types of MOSFET.   | <b>01</b>       |
| <br><b>Q-2</b> | <br><b>Attempt all questions</b>  | <br><b>(14)</b> |
|                | <b>a.</b> Write a note on GaAs and InGaAs HBTs in detail.   | <b>07</b>       |
|                | <b>b.</b> Write a note on the requirements of BJT and explain the demands, problems and solutions required for BJT. | <b>07</b>       |
|                | <b>OR</b>   |                 |
| <br><b>Q-2</b> | <br><b>Attempt all questions</b>  | <br><b>(14)</b> |
|                | <b>a.</b> Explain and discuss with necessary diagram JFET and MESFET in detail.                                     | <b>14</b>       |
| <br><b>Q-3</b> | <br><b>Attempt all questions</b>  | <br><b>(14)</b> |
|                | <b>a.</b> Write a note on effects in real devices in JFET in detail.  | <b>07</b>       |
|                | <b>b.</b> Explain in detail the small signal characteristics of MESFETs.  | <b>07</b>       |
|                | <b>OR</b>   |                 |
| <br><b>Q-3</b> | <br><b>Attempt all questions</b>  | <br><b>14</b>   |
|                | <b>a.</b> Write a note on MOS capacitor in detail with necessary diagrams and explain its three important regions.  | <b>14</b>       |



## SECTION – II

- Q-4 Attempt the Following questions (07)**
- a. Why polysilicon gate is used instead of metal gate? 01
  - b. Define Depletion in MOSFET. 01
  - c. What is Beer- Lambert law. 01
  - d. What do you mean by signal (beam) steering? 01
  - e. What is direct band gap? 01
  - f. List out the three mechanisms for the recombination in LED. 01
  - g. Write the principle of solar cell. 01
- Q-5 Attempt all questions (14)**
- a Write a note on PIN photodetector. 07
  - b Explain in detail about LEDs. 07
- OR**
- Q-5 Attempt all questions**
- a Write a note on laser structure and optical cavity. 07
  - b Explain in detail optical absorption and derive absorption coefficient. 07
- Q-6 Attempt all questions (14)**
- a What do you mean by double heterojunction LEDs? Explain in detail. 07
  - b Write a note on avalanche photodiode with necessary diagram. 07
- OR**
- Q-6 Attempt all Questions**
- a Write a note on LASERs: Quantum well, wire and dot. 07
  - b Explain in detail about n-channel and p-channel enhancement type MOSFETs with necessary diagrams. 07

